

L Number	Hits	Search Text	DB	Time stamp
1	50	corning adj glass adj "7059"	USPAT	2003/06/12 11:18
2	1	us-5622814-\$.did. and (al aluminum)	USPAT	2003/06/12 11:38
3	9110	active adj matrix	USPAT	2003/06/12 11:40
4	39	(active adj matrix) with repeat\$3	USPAT	2003/06/12 11:47
5	6356	microelectromechanical adj system adj device mems!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
6	27721	active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
7	10	(microelectromechanical adj system adj device mems!) with (active adj matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
8	2	((active adj matrix) with repeat\$3) and 430/\$.ccls.	USPAT	2003/06/12 11:47
9	4100	(semiconductor) with repeat\$3	USPAT	2003/06/12 11:48
10	369	((semiconductor) with repeat\$3) and 430/\$.ccls.	USPAT	2003/06/12 11:48
11	2011	(semiconductor) with repeat\$3 with (step method process)	USPAT	2003/06/12 11:50
12	225	((semiconductor) with repeat\$3 with (step method process)) and 430/\$.ccls.	USPAT	2003/06/12 11:50
14	225	((semiconductor) with repeat\$3 with (step method process)) and 430/\$.ccls.) and 430/\$.ccls.	USPAT	2003/06/12 11:51
15	22	((semiconductor) with repeat\$3 with (step method process) with (known typical\$3 conventional\$3)) and 430/\$.ccls.	USPAT	2003/06/12 11:51
16	2909	(backside back-side back adj side) near2 (expos\$4 irradiat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:26
17	1	((semiconductor) with repeat\$3 with (step method process)) same ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:55
18	15	((semiconductor) with repeat\$3 with (step method process)) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:55
19	0	(semiconductor) with repeat\$3 with (step method process) with (known typical\$3 conventional\$3) with (many multiple) with layer	USPAT	2003/06/12 11:57
20	3	(semiconductor) with repeat\$3 with (step method process) with (known typical\$3 conventional\$3) with (many multiple)	USPAT	2003/06/12 11:57
13	130	(semiconductor) with repeat\$3 with (step method process) with (known typical\$3 conventional\$3)	USPAT	2003/06/12 11:59
21	85	(semiconductor) with repeat\$3 with (steps! method process) with (known typical\$3 conventional\$3)	USPAT	2003/06/12 12:10
22	2	(semiconductor) with repeat\$3 with (steps! method process) with (required) with (multiple near2 layer)	USPAT	2003/06/12 12:11
23	0	(electrodes) with repeat\$3 with (steps! method process) with (required) with (multiple near2 layer)	USPAT	2003/06/12 12:12
24	1789	(electrodes) with repeat\$3 with (steps! method process)	USPAT	2003/06/12 12:13
25	58	(electrodes) with repeat\$3 with (steps! method process) with (known conventional\$2 typical\$2)	USPAT	2003/06/12 12:18
26	323	(pattern) with repeat\$3 with (steps! method process) with (known conventional\$2 typical\$2)	USPAT	2003/06/12 12:18

27	81	(438/\$.ccls. 430/\$.ccls.) and ((pattern) with repeat\$3 with (steps! method process) with (known conventional\$2 typical\$2))	USPAT	2003/06/12 12:19
28	11941	(back) near2 (expos\$4 irradiat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:26
29	10292	((back) near2 (expos\$4 irradiat\$5)) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:27
30	151	((back) near2 (expos\$4 irradiat\$5)) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))) same repeat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:28
31	63	((back) near2 (expos\$4 irradiat\$5)) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))) same (repeat\$3 with (steps method process))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:32
32	2	("5707785").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:32
-	26	MILES-MARK-.in. MILES-MARK-W-.in. MILES-M-W-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/11 16:34
-	2907	(backside back-side back adj side) near2 (expos\$4 irradiat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:52
-	398591	resist photoresist photo-resist	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:38
-	311632	photosensitive photo-sensitive (sensitive near (photo light energy radiation))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:39
-	357428	uv ultraviolet ultra-violet ultra adj violet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:40
-	32060	((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:46
-	24	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative) same (uv ultraviolet ultra-violet ultra adj violet)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:32
-	2	("5674757").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:34
-	6323	microelectromechanical adj system adj device mems!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
-	34	(microelectromechanical adj system adj device mems!) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:04

-	7	(microelectromechanical adj system adj device mems!) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) and (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:44
-	28	(ni nickel al aluminum) same ((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:52
-	177	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:57
-	4	((((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:55
-	17	((((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) not (((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:55
-	50	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (transvers\$4 longitudinal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:58
-	6	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (transvers\$4 longitudinal\$4)) and ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) 430/\$.CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:01
-	2	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) SAME (microelectromechanical adj system adj device mems!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:01
-	1003	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) (uv ultraviolet ultra-violet ultra adj violet) laser mask photomask light)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:07
-	584	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) (uv ultraviolet ultra-violet ultra adj violet) (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative) mask photomask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:11

-	410	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) (uv ultraviolet ultra-violet ultra adj violet) (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative) mask photomask)	USPAT; US-PGPUB	2003/06/11 18:12
-	58	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) (uv ultraviolet ultra-violet ultra adj violet) mask photomask)) same negative	USPAT; US-PGPUB	2003/06/11 18:59
-	1	us-6304309-\$.did. and (orthogonal\$3 transvers\$5)	USPAT; US-PGPUB	2003/06/11 19:01
-	324	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) and (orthogonal\$3 transvers\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 19:01
-	18	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (orthogonal\$3 transvers\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 19:03
-	23	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) and (layer same (orthogonal\$3 transvers\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:16